

THE CL055 (PNP) AND CL066 (NPN) ARE SILICON PLANAR EPITAXIAL COMPLEMENTARY PAIR SPECIALLY DESIGNED FOR 1-WATT AUDIO AMPLIFIER OUTPUT AND SWITCHING APPLICATIONS. THEY FEATURE LOW COLLECTOR-EMITTER KNEE VOLTAGE AND GOOD LINEARITY OF D.C. CURRENT GAIN.

CASE TO-92A



ABSOLUTE MAXIMUM RATINGS

For p-n-p devices, voltage and current values are negative

Collector-Base Voltage	VCBO	25V
Collector-Emitter Voltage	VCEO	20V
Emitter-Base Voltage	VEBO	5V
Collector Current	Ic	1A
Collector Peak Current (t ≤ 50ms)	ICM	1.5A
Total Power Dissipation @ TC ≤ 25°C	Ptot	1.5W
Without Heat Sink @ TA ≤ 25°C		625mW
Operating Junction & Storage Temperature	Tj, Tstg	-55 to 150°C

ELECTRICAL CHARACTERISTICS (TA = 25°C unless otherwise noted)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	TEST CONDITIONS
Collector-Base Breakdown Voltage	BVCBO	25			V	Ic=100µA IE=0
Collector-Emitter Breakdown Voltage	LVCEO *	20			V	Ic=10mA IB=0
Collector-Emitter Cutoff Current	ICES			0.5	µA	VCE=20V VBE=0
Emitter-Base Cutoff Current	IEBO			1.0	µA	VEB=5V IC=0
Collector-Emitter Knee Voltage	VCEK		0.25	0.5	V	Ic=0.2A IB=value at which Ic=0.22A VCE=1V
Collector-Emitter Saturation Voltage	VCE(sat)*		0.21	0.4	V	Ic=0.5A IB=0.05A
Base-Emitter Voltage	VBE *		0.87	1.2	V	Ic=0.5A VCE=1V
D.C. Current Gain (Note)	HFE 1 *	50	160	360		Ic=0.1A VCE=1V
	HFE 2 *	20	80			Ic=1A VCE=2V
Current Gain-Bandwidth Product	fT		120		MHz	Ic=50mA VCE=10V

Note : HFE 1 is classified as follows.

Group A : 50-100
Group C : 120-240

Group B : 80-160
Group D : 180-360

* Pulse Test : Pulse Width=0.3ms, Duty Cycle=1%



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